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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Tuller et al. GROUP: 2811
SERIAL NO: 10/663,531 EXAMINER: Unknown
FILED: 09/16/2003
FOR: METHOD FOR P-TYPE DOPING WIDE BAND GAP OXIDE SEMICONDUCTORS

Mail Stop DD
Commissioner of Patents
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INFORMATION DISCLOSURE STATEMENT

In compliance with 37 C.F.R. §§1.56, 1.97, and 1.98, Applicant submits copies of the documents listed on the attached Form PTO-1449.

The listed documents were recently cited in a corresponding PCT application, and a copy of the International Search Report is being submitted herewith for purposes of convenience.

The Commissioner is authorized to charge Deposit Order Account No. 19-0079 for any further fee that is required.

Respectfully submitted,

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I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to the Mail Stop DD, Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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Date

FORM PTO-1449
(Rev. 5/92)GAUTHIER & CONNORS LLP
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ATTORNEY DOCKET NO.10/663,531
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STATEMENT BY APPLICANTAPPLICANT: Tuller et al.
FILING DATE: 09/16/2003

GROUP: 2811

EXAMINER: Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AJ	1 115 163 A1	07/11/2001	EP			YES
	AK	1 199 755 A1	04/24/2002	EP			YES
	AL	1 349 203 A2	10/01/2003	EP			YES
	AM						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AN	"Thermally stable, highly conductive, and transparent ZnO layers prepared in situ by chemical vapor deposition," Ataev et al. <i>Materials and Science Engineering</i> . 1999. Vol. B 65.
	AO	"Growth of P-Type Zinc oxide films by chemical vapor deposition," Minegishi et al. <i>Jpn. J. Appl. Phys.</i> November 1997. Vol. 36. Part 2, No. 11A.
	AP	"Performances presented by zinc oxide thin films deposited by spray pyrolysis," Nunes et al. <i>Thin Solid Films</i> . 1999. Vol. 337.
	AQ	"Optical and electrical characteristics of aluminum-doped ZnO thin films prepared by solgel technique," Jimenez-Gonzalez et al. <i>Journal of Crystal Growth</i> . 1998. Vol. 192.

EXAMINER

DATE CONSIDERED

EXAMINER:

Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.